ABSTRACT

The semiconductor device comprises a substrate, a semiconductor element mounted on the substrate, a heat diffusion member mounted on the substrate while covering the semiconductor element, and a resin seal for covering the semiconductor element. An integrated capacitor is mounted on the heat diffusion member in an opposed relationship to the semiconductor element and electrically connected to the semiconductor element. The integrated capacitor and the semiconductor element are electrically connected over a distance as shortest as possible. The heat diffusion member includes a first conductive layer and a second conductive layer isolated from each other by an insulating layer, some terminals of the integrated capacitor are connected to the corresponding terminals of the substrate through the first conductive layer, and the other terminals of the integrated capacitor are connected to the corresponding terminals of the substrate through the second conductive layer. Thus, an increase of inductance due to additional capacitors can be restricted.